

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC2880

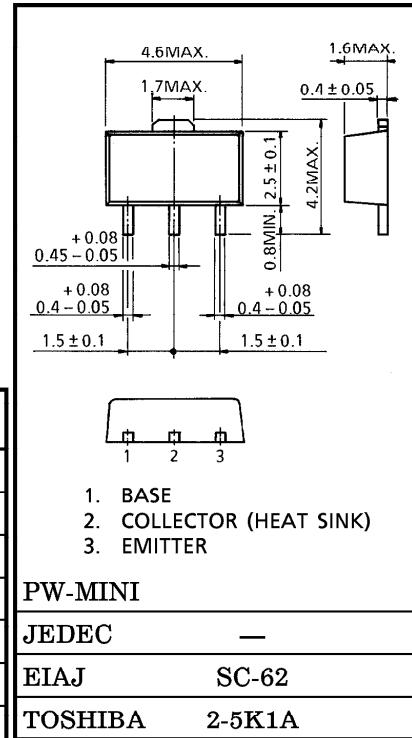
HIGH VOLTAGE SWITCHING APPLICATIONS.

Unit in mm

- High Voltage : $V_{CEO} = 150V$
- High Transition Frequency : $f_T = 120MHz$
- $P_C = 0.8 \sim 2W$ (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1200

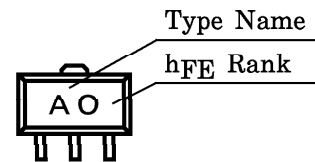
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Base Current	I_B	10	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C (Note)	800	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$



Weight : 0.05g

Marking



Note : Mounted on ceramic substrate (250mm²×0.8t)

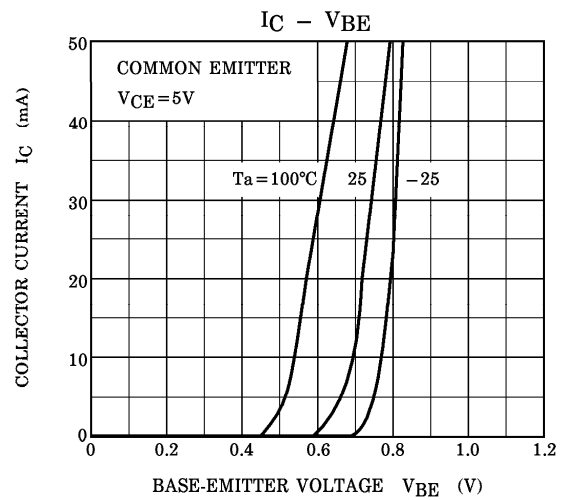
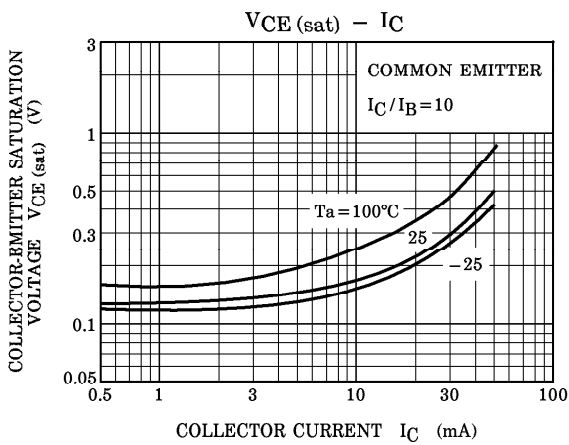
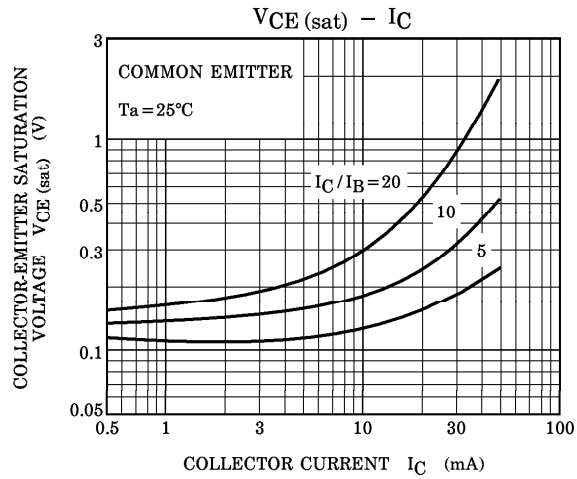
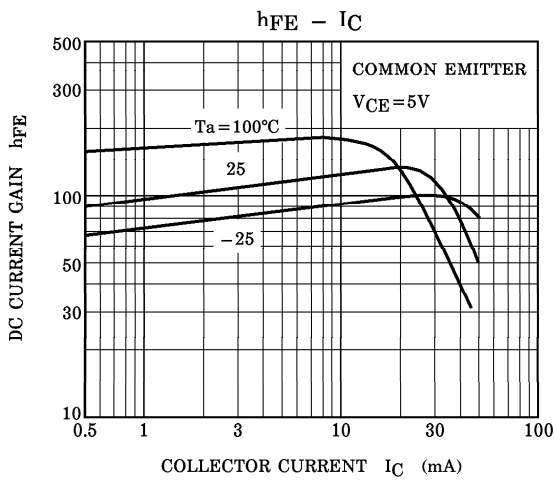
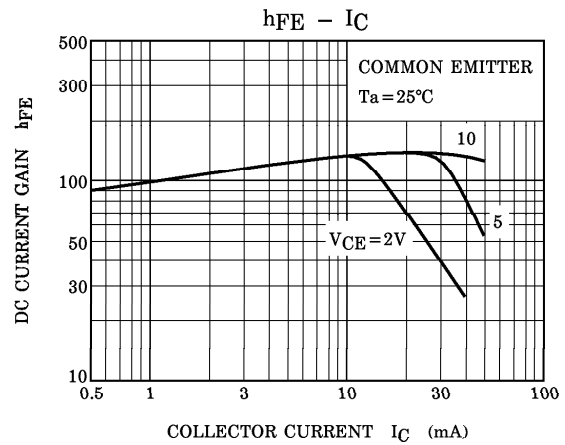
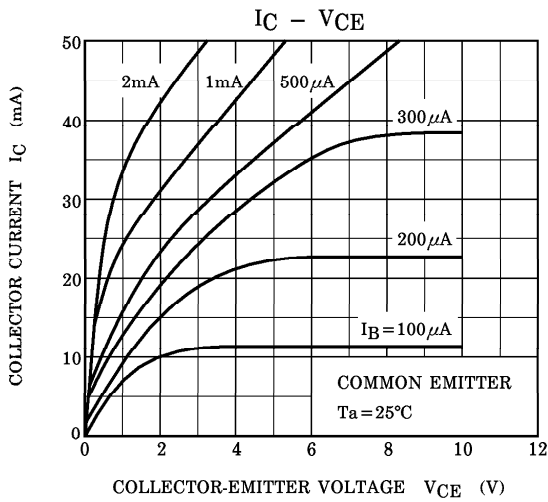
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 200V, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE} = 5V, I_C = 10mA$	70	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$	—	—	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5V, I_C = 30mA$	—	—	1	V
Transition Frequency	f_T	$V_{CE} = 30V, I_C = 10mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3.5	5.0	pF

Note : h_{FE} Classification O : 70~140, Y : 120~240

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